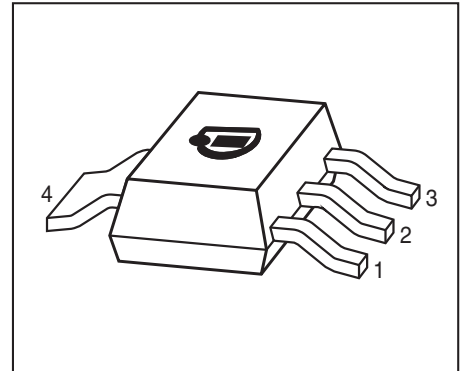


**PNP Silicon AF Transistor**

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary type: BCP68 (NPN)
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



Type	Marking	Pin Configuration						Package
		1=B	2=C	3=E	4=C	-	-	
BCP69-25	...-25*	1=B	2=C	3=E	4=C	-	-	SOT223

\* Marking is the same than type-name

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	20	V
Collector-emitter voltage	$V_{CES}$	25	
Collector-base voltage	$V_{CBO}$	25	
Emitter-base voltage	$V_{EBO}$	5	
Collector current	$I_C$	1	A
Peak collector current, $t_p \leq 10$ ms	$I_{CM}$	2	
Base current	$I_B$	100	mA
Peak base current	$I_{BM}$	200	
Total power dissipation- $T_S \leq 114$ °C	$P_{tot}$	3	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-65 ... 150	

<sup>1)</sup>Pb-containing package may be available upon special request

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 12$	K/W

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics**

Collector-emitter breakdown voltage $I_C = 30\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	20	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	25	-	-	
Collector-emitter breakdown voltage $I_C = 10\text{ }\mu\text{A}, V_{BE} = 0$	$V_{(BR)CES}$	25	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}, I_C = 0$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 25\text{ V}, I_E = 0$ $V_{CB} = 25\text{ V}, I_E = 0, T_A = 150\text{ }^\circ\text{C}$	$I_{CBO}$	-	-	0.1 100	$\mu\text{A}$
DC current gain <sup>2)</sup> $I_C = 5\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}, V_{CE} = 1\text{ V}, \text{BCP69-16}$ $I_C = 500\text{ mA}, V_{CE} = 1\text{ V}, \text{BCP69-25}$ $I_C = 1\text{ A}, V_{CE} = 1\text{ V}$	$h_{FE}$	50 100 160 60	- 160 250 -	- 250 375 -	-
Collector-emitter saturation voltage <sup>2)</sup> $I_C = 1\text{ A}, I_B = 100\text{ mA}$	$V_{CEsat}$	-	-	0.5	V
Base-emitter voltage <sup>2)</sup> $I_C = 5\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1\text{ A}, V_{CE} = 1\text{ V}$	$V_{BE(ON)}$	- -	0.6 -	- 1	

**AC Characteristics**

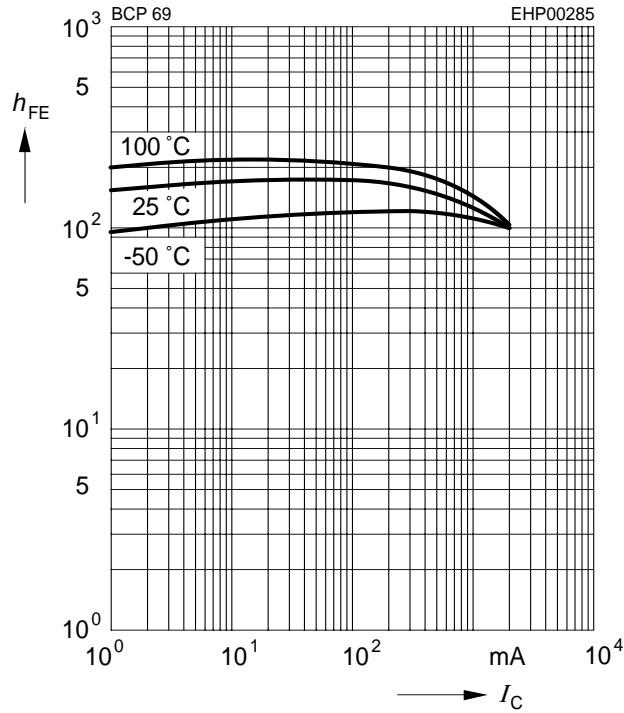
Transition frequency $I_C = 100\text{ mA}, V_{CE} = 5\text{ V}, f = 100\text{ MHz}$	$f_T$	-	100	-	MHz
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<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

<sup>2</sup>Pulse test:  $t < 300\mu\text{s}; D < 2\%$

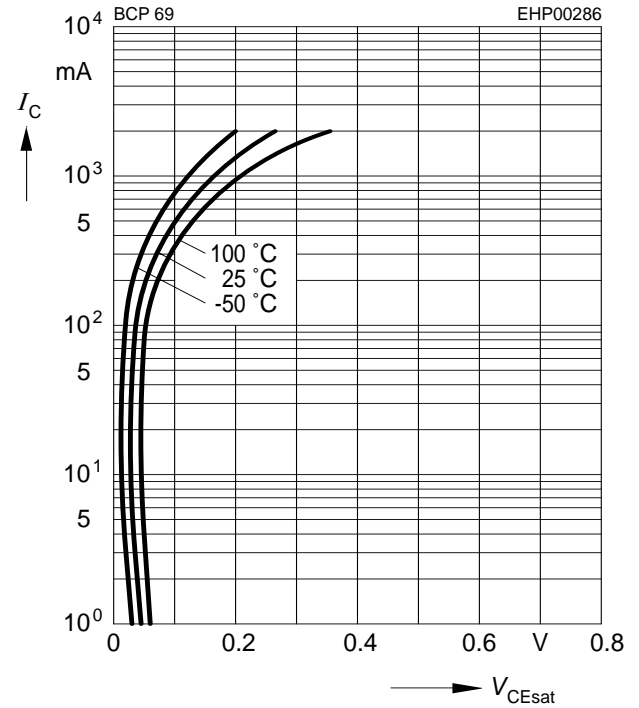
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 1\text{ V}$



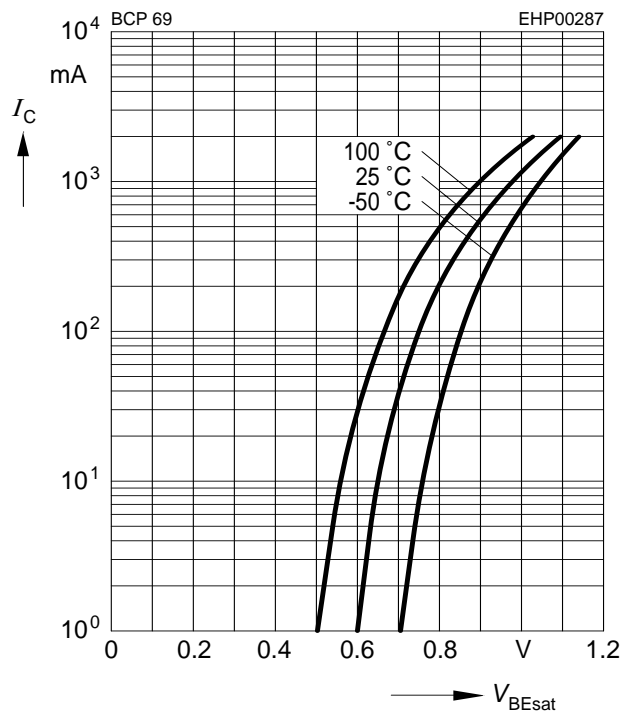
**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat}), h_{FE} = 10$



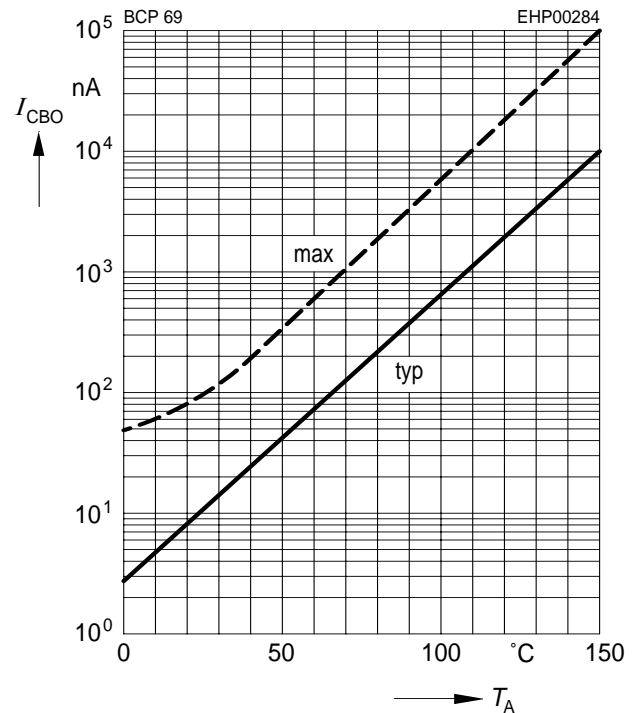
**Base-emitter saturation voltage**

$I_C = f(V_{BEsat}), h_{FE} = 10$



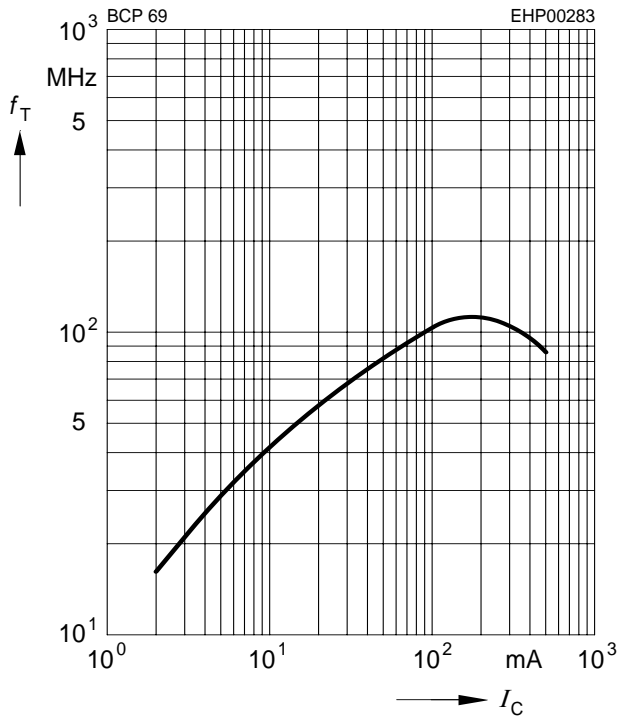
**Collector cutoff current  $I_{CBO} = f(T_A)$**

$V_{CBO} = 25\text{ V}$

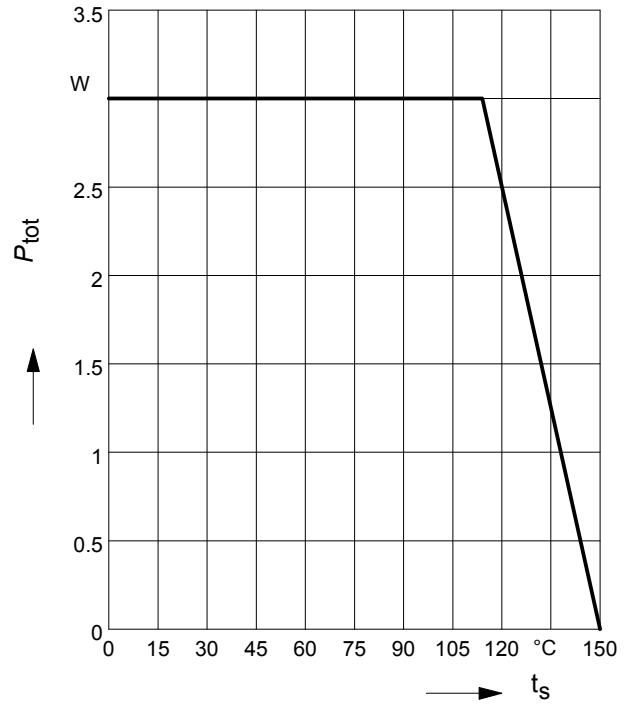


Transition frequency  $f_T = f(I_C)$

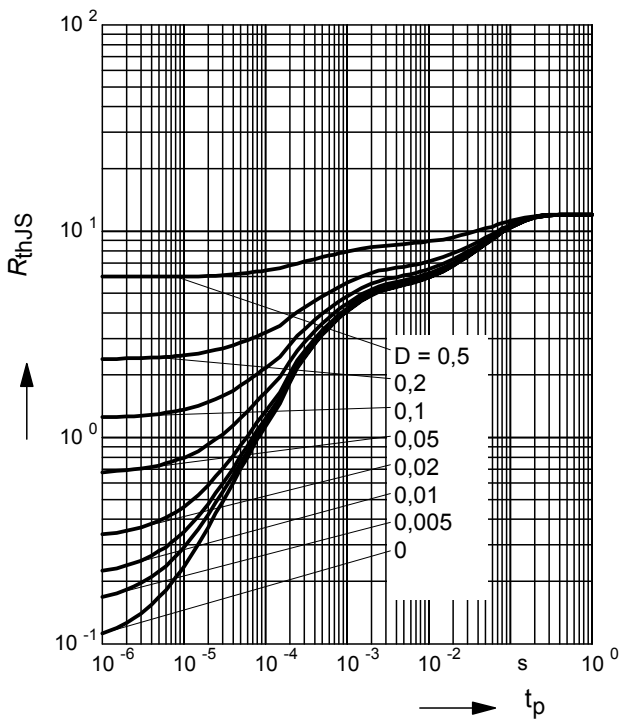
$V_{CE} = 5\text{ V}$



Total power dissipation  $P_{tot} = f(T_S)$

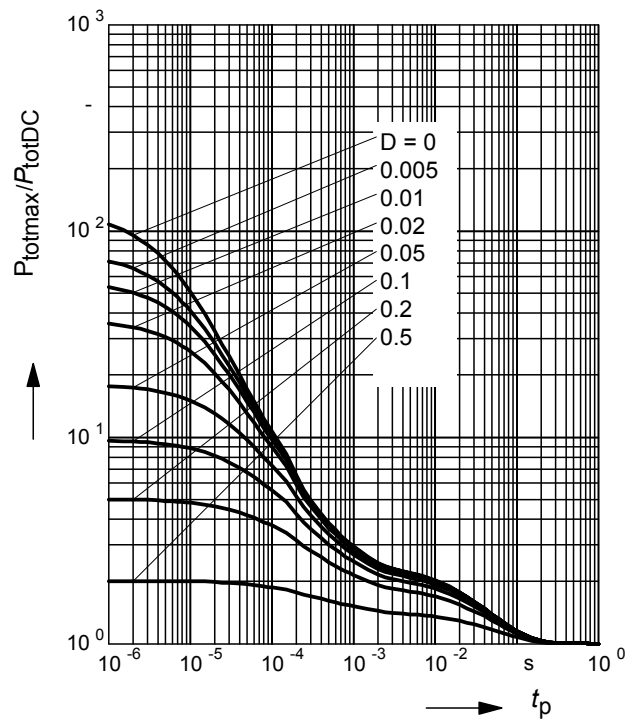


Permissible Pulse Load  $R_{thJS} = f(t_p)$

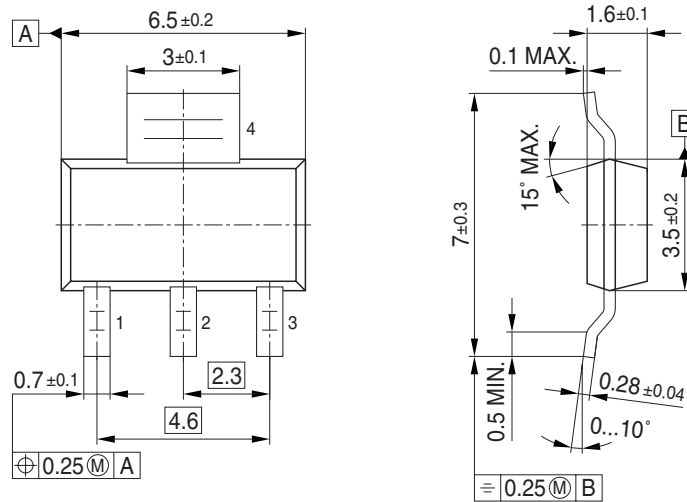


Permissible Pulse Load

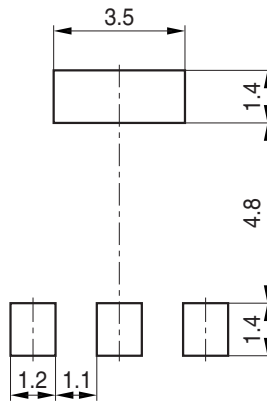
$P_{totmax}/P_{totDC} = f(t_p)$



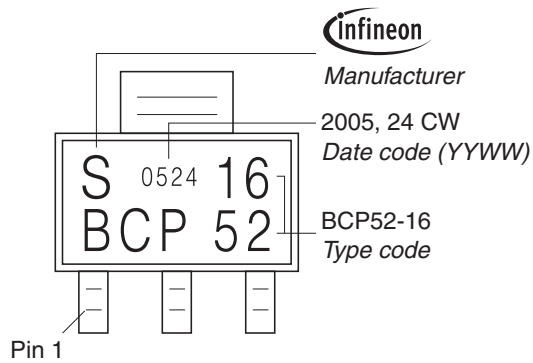
Package Outline



Foot Print

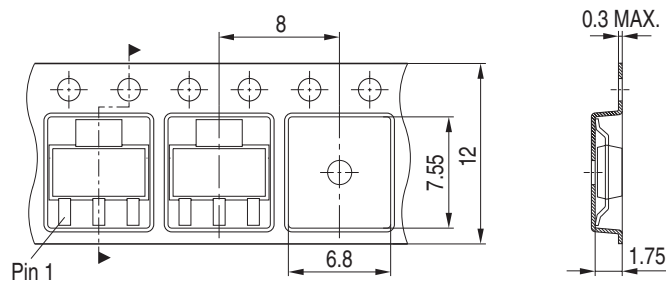


Marking Layout (Example)



Packing

Reel  $\varnothing 180 \text{ mm} = 1.000 \text{ Pieces/Reel}$   
 Reel  $\varnothing 330 \text{ mm} = 4.000 \text{ Pieces/Reel}$



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